



30V P-CHANNEL ENHANCEMENT MODE MOSFET PowerDI®

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _A = 25°C
	17mΩ @ V _{GS} = -10V	-8.6A
-30V	25mΩ @ V _{GS} = -4.5V	-7.1A

Features and Benefits

- Low R_{DS(ON)} Ensures On-State Losses are Minimized
- Small Form Factor Thermally Efficient Package Enables Higher Density End Products
- Occupies Just 33% of the Board Area Occupied by SO-8 Enabling Smaller End Product
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

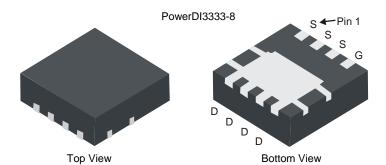
Description and Applications

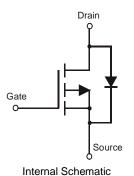
This MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$), yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Backlighting
- Power Management Functions
- DC-DC Converters

Mechanical Data

- Case: PowerDI[®]3333-8
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202. Method 208 @3
- Weight: 0.008 grams (Approximate)





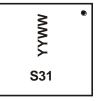
Ordering Information (Note 5)

Part Number	Case	Packaging
DMP3008SFGQ-7	PowerDI3333-8	2,000/Tape & Reel
DMP3008SFGQ-13	PowerDI3333-8	3.000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product_compliance_definitions/.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



S31 = Product Type Marking Code YYWW = Date Code Marking YY = Last digit of year (ex: 11 = 2011) WW = Week code (01 ~ 53)

PowerDI is a registered trademark of Diodes Incorporated.



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

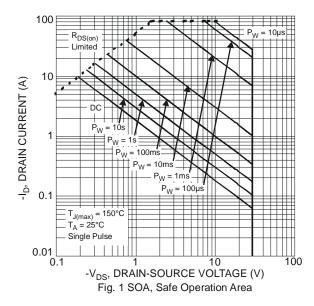
Characteristic	Symbol	Value	Units		
Drain-Source Voltage	V _{DSS}	-30	V		
Gate-Source Voltage	V _{GSS}	±20	V		
Operitoring Projet Operand (Note 7) V 40V	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I _D	-8.6 -7.0	А
Continuous Drain Current (Note 7) V _{GS} = -10V	t<10s	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I _D	-11.7 -9.3	А
Continuous Dusin Compant (Nata 7) \	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I _D	-7.1 -5.6	А
Continuous Drain Current (Note 7) V _{GS} = -4.5V	t<10s	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I _D	-9.6 -7.6	А
Pulsed Drain Current (10µs pulse, duty cycle = 1%)	I _{DM}	-80	А		
Maximum Continuous Body Diode Forward Current (I _S	-3.0	Α		

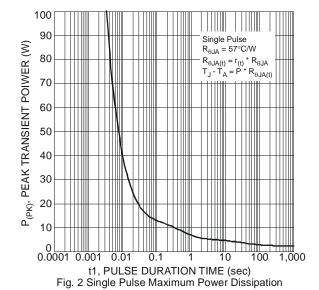
Thermal Characteristics

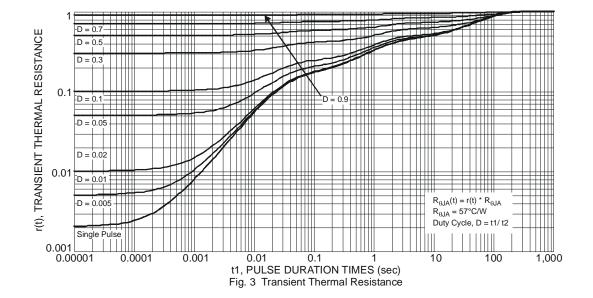
Characteristic	Symbol	Value	Units	
Total Power Dissipation (Note 6)		P_{D}	0.9	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	2	140	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	t<10s	$R_{\theta JA}$	72	°C/W
Total Power Dissipation (Note 7)		P_{D}	2.2	W
Thermal Resistance, Junction to Ambient (Note 7)	Steady State	D	57	°C/W
Thermal Resistance, Junction to Ambient (Note 1)	t<10s	$R_{\theta JA}$	30	°C/W
Thermal Resistance, Junction to Case (Note 7)		R ₀ JC	7.1	°C/W
Operating and Storage Temperature Range		$T_{J_i}T_{STG}$	-55 to +150	°C

6. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout. 7. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.











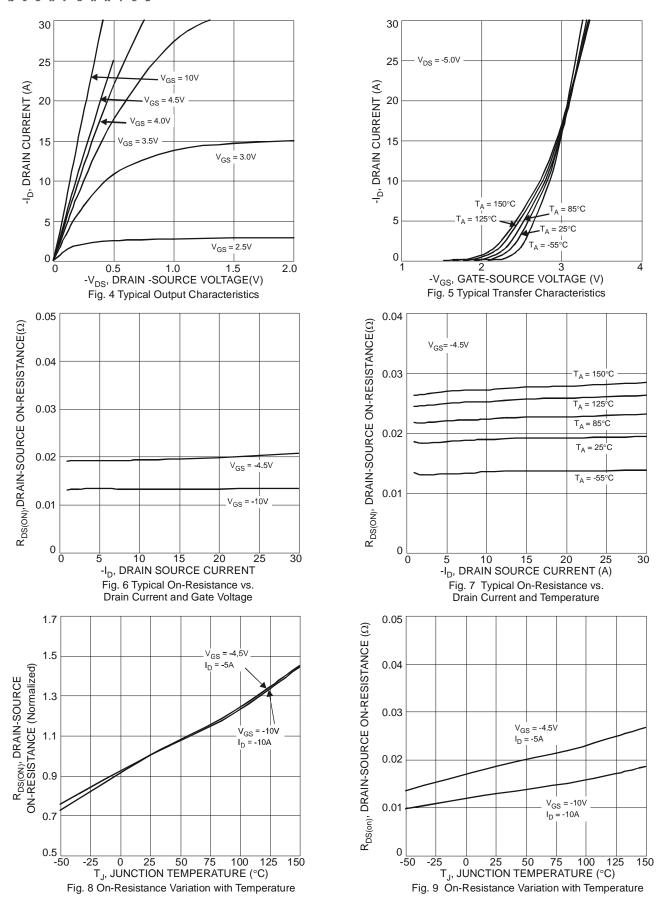
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage	BV _{DSS}	-30	_	_	V	$V_{GS} = 0V, I_D = -250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	-1.0	μΑ	$V_{DS} = -30V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	V _{GS(th)}	-1.1	-1.6	-2.1	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	
Static Drain-Source On-Resistance			12.5	17	mΩ	$V_{GS} = -10V, I_D = -10A$	
Static Diain-Source On-Nesistance	R _{DS(ON)}		18.5	25		$V_{GS} = -4.5V, I_D = -10A$	
Forward Transfer Admittance	Y _{fs}		13	_	S	$V_{DS} = -15V, I_{D} = -10A$	
Diode Forward Voltage	V_{SD}		-0.7	-1.0	V	$V_{GS} = 0V, I_{S} = -1A$	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	Ciss	_	2,230	_		V 45V V 6V	
Output Capacitance	Coss		328	_	pF	$V_{DS} = -15V, V_{GS} = 0V$ f = 1.0MHz	
Reverse Transfer Capacitance	C_{rss}		294	_		I = I.ONIAZ	
Gate Resistance	Rg	_	6.4	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1.0MHz$	
Total Gate Charge (V _{GS} = -10V)	Qg	_	47	_			
Total Gate Charge (V _{GS} = -4.5V)	Qg	_	23	_	nC	\\\ 45\\ I 400	
Gate-Source Charge	Qgs	_	9.4	_	iiC	$V_{DS} = -15V, I_{D} = -10A$	
Gate-Drain Charge	Q _{gd}	_	5.6	_			
Turn-On Delay Time	t _{D(ON)}	_	10.5	_			
Turn-On Rise Time	t _R		8.5		nS	V 10V V 15V D 00	
Turn-Off Delay Time	t _{D(OFF)}	_	90	_	113	$V_{GS} = -10V, V_{DS} = -15V, R_G = 6\Omega$	
Turn-Off Fall Time	t _F	_	40	_			

Notes:

^{8.} Short duration pulse test used to minimize self-heating effect. 9. Guaranteed by design. Not subject to product testing.







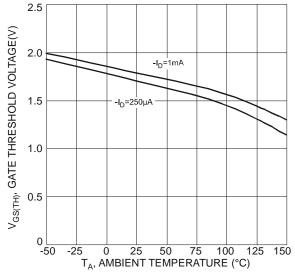
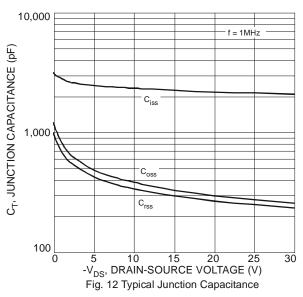
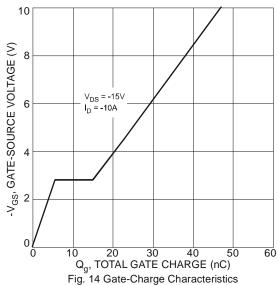
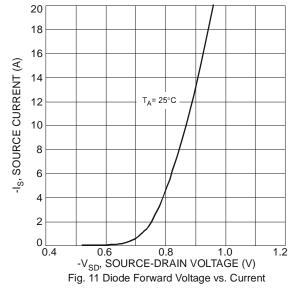


Fig. 10 Gate Threshold Variation vs. Ambient Temperature







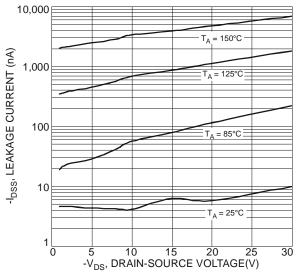


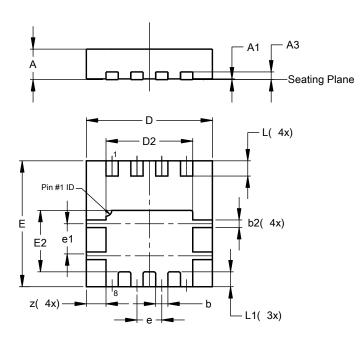
Fig. 13 Typical Drain-Source Leakage Current vs. Voltage



Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.

PowerDI3333-8

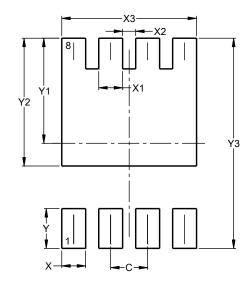


PowerDI3333-8					
Dim	Min	Max	Тур		
Α	0.75	0.85	0.80		
A1	0.00	0.05	0.02		
A3	_	_	0.203		
b	0.27	0.37	0.32		
b2	_	_	0.20		
D	3.25	3.35	3.30		
D2	2.22	2.32	2.27		
Е	3.25	3.35	3.30		
E2	1.56	1.66	1.61		
е	_	_	0.65		
e1	0.79	0.89	0.84		
L	0.35	0.45	0.40		
L1	_	_	0.39		
Z	_	_	0.515		
All Dimensions in mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.

PowerDI3333-8



Dimensions	Value (in mm)		
С	0.650		
X	0.420		
X1	0.420		
X2	0.230		
Х3	2.370		
Υ	0.700		
Y1	1.850		
Y2	2.250		
Y3	3.700		



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DMP3008SFGQ Document number: DS38141 Rev. 1 - 2

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